



THE DATASHEET OF MPSW42G

MPSW42

One Watt High Voltage Transistor

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	300	Vdc
Collector – Base Voltage	V_{CBO}	300	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

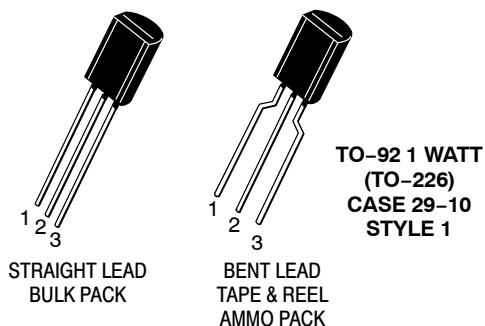
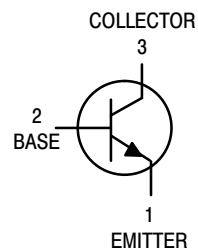
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

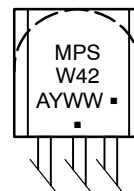


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MARKING DIAGRAM



MPSW42 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MPSW42	TO-92	5000 Units/Box
MPSW42G	TO-92 (Pb-Free)	5000 Units/Box
MPSW42RLRA	TO-92	2000/Tape & Reel
MPSW42RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MPSW42

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	300	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = 100 µA _{dc} , I _E = 0)	V _{(BR)CBO}	300	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 100 µA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	–	V _{dc}
Collector Cutoff Current (V _{CB} = 200 V _{dc} , I _E = 0)	I _{CBO}	–	0.1	µA _{dc}
Emitter Cutoff Current (V _{EB} = 6.0 V _{dc} , I _C = 0)	I _{EBO}	–	0.1	µA _{dc}
ON CHARACTERISTICS				
DC Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 30 mA _{dc} , V _{CE} = 10 V _{dc})	h _{FE}	25 40 40	– – –	–
Collector–Emitter Saturation Voltage (I _C = 20 mA _{dc} , I _B = 2.0 mA _{dc})	V _{CE(sat)}	–	0.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = 20 mA _{dc} , I _B = 2.0 mA _{dc})	V _{BE(sat)}	–	0.9	V _{dc}
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (I _C = 10 mA _{dc} , V _{CE} = 20 V _{dc} , f = 20 MHz)	f _T	50	–	MHz
Collector Capacitance (V _{CB} = 20 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{cb}	–	3.0	pF

1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

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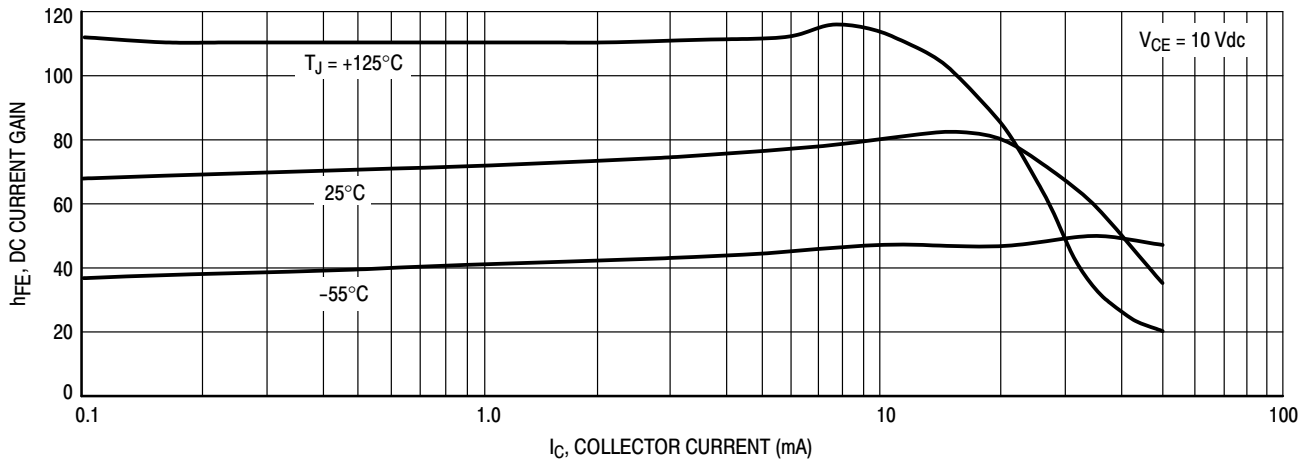


Figure 1. DC Current Gain

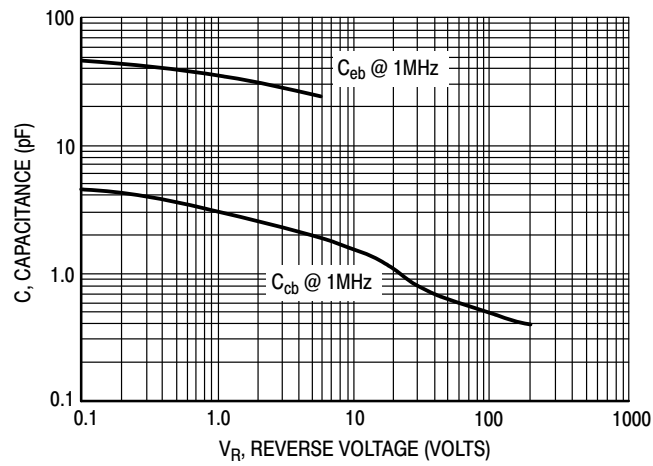


Figure 2. Capacitance

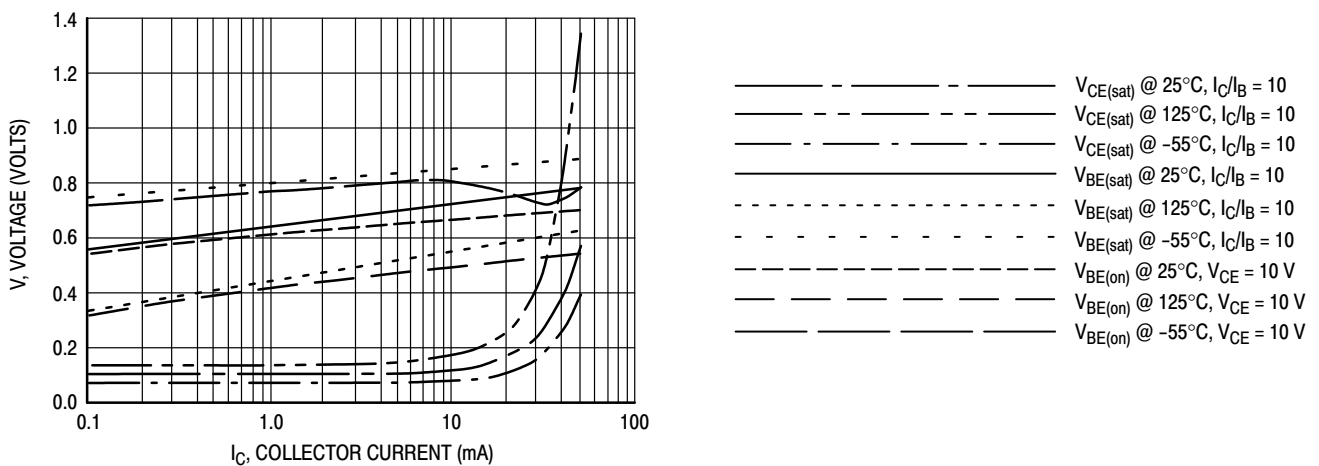


Figure 3. "ON" Voltages

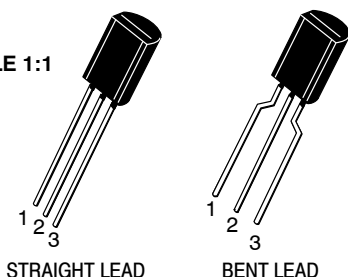
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



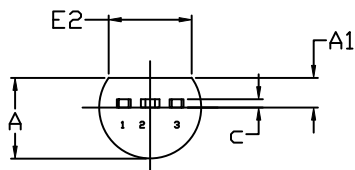
STRAIGHT LEAD

BENT LEAD

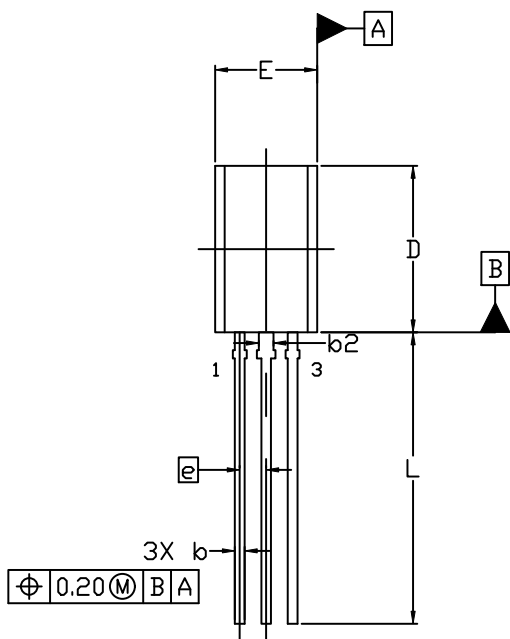
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DATE 05 MAR 2021

STRAIGHT LEAD



END VIEW



TOP VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

STYLES AND MARKING ON PAGE 3

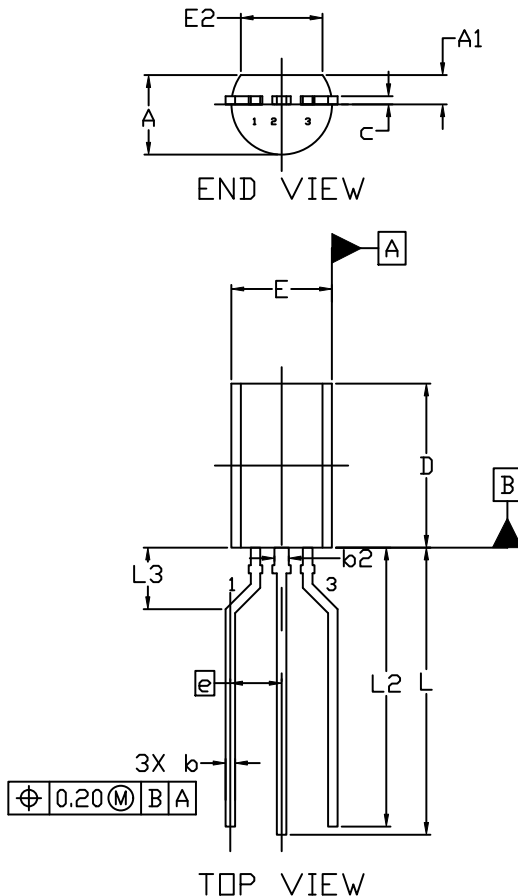
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DATE 05 MAR 2021

FORMED LEAD



NOTES:

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b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

STYLES AND MARKING ON PAGE 3

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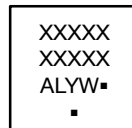
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DATE 05 MAR 2021

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V _{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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